

- Analytical Simulation of L-I Characteristics for AR/HR Coated Double-Heterostructure AlGaAs/GaAs/AlGaAs Diode-Lasers Operating at 890 nm.

Chetan Panchal, **Vipul Kheraj**, Krish Chalpathi, Tarun Sharma, Brij Mohan Arora  
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- Effect of Facet Reflectivities on High-power Highly Strained InGaAs Quantum-well Diode Lasers Operating at 1.2 $\mu$ m.

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- L-I Characteristics of AR–HR Coated AlGaAs LPE Grown Laser Diodes.

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